



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

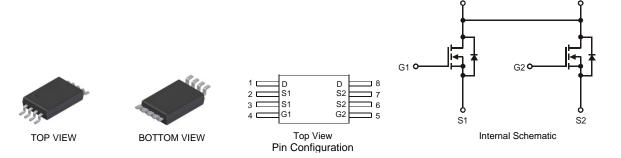
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D

D1

- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.039 grams (approximate)



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	4.9 3.9	А
Pulsed Drain Current (Note 2)			I _{DM}	31	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _D	0.87	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{θJA}	143	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 2. Repetitive rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

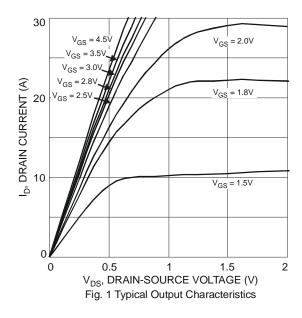


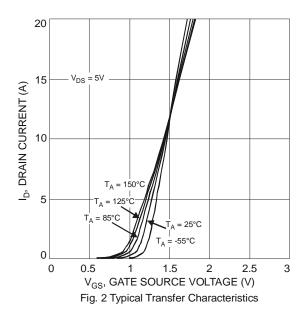
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	0.5	-	0.9	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		-	19	-	mΩ	$V_{GS} = 4.5V, I_D = 8.2A$	
Static Drain-Source On-Resistance	R _{DS (ON)}		22			$V_{GS} = 2.5V, I_D = 3.3A$	
			28	37		$V_{GS} = 1.8V, I_D = 2.0A$	
Forward Transfer Admittance	Y _{fs}	-	7	-	S	$V_{DS} = 10V, I_D = 4A$	
Diodes Forward Voltage	V_{SD}	-	0.7	0.9	V	Is = 2.25A, V _{GS} = 0V	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	841	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	88	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	81	-	pF	71 = 1.0WHZ	
Gate Resistance	R_g	-	1.24	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Q_{g}	-	9.6	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 8.2A$	
Gate-Source Charge	Q_{gs}	-	1.4	-	nC		
Gate-Drain Charge	Q_{gd}	-	2.1	-	nC		
Turn-On Delay Time	t _{D(on)}	-	7.8	-	ns		
Turn-On Rise Time	t _r	-	21.1	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	38.6	-	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f	-	10.1	-	ns		

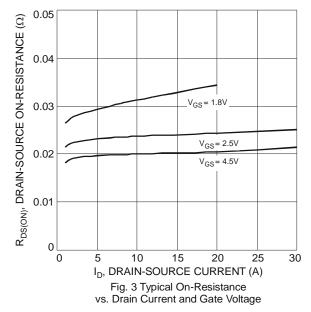
Notes:

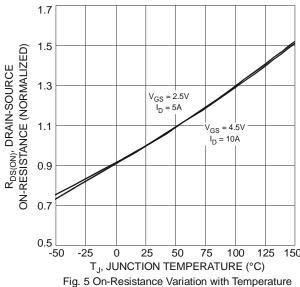
- 5. Short duration pulse test used to minimize self-heating effects.6. Guaranteed by design. Not subject to production testing.











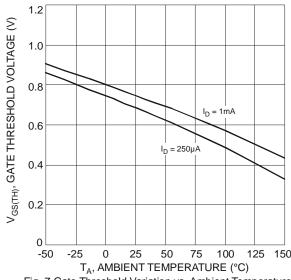


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

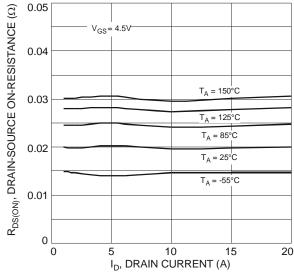


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

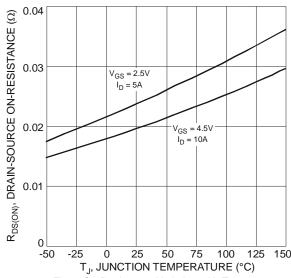


Fig. 6 On-Resistance Variation with Temperature

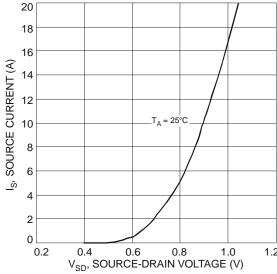
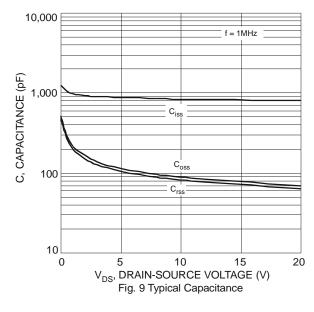


Fig. 8 Diode Forward Voltage vs. Current





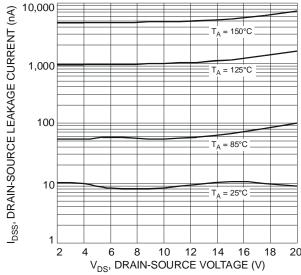


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

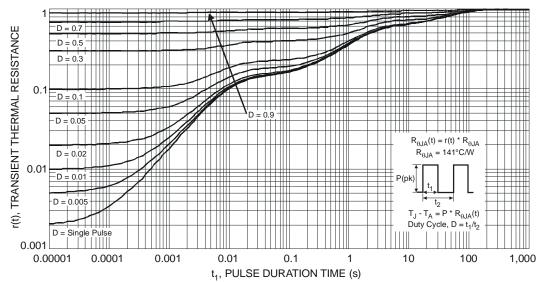


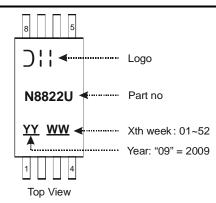
Fig. 11 Transient Thermal Response

Ordering Information (Note 7)

Part Number	Case	Packaging
DMG8822UTS-13	TSSOP-8L	2500 / Tape & Reel

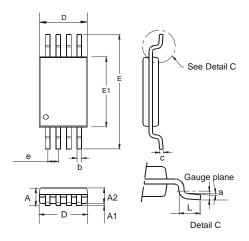
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



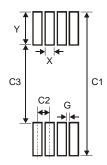


Package Outline Dimensions



TSSOP-8L				
Dim	Min	Max	Тур	
а	0.09	-	_	
Α	_	1.20	_	
A1	0.05	0.15	_	
A2	0.825	1.025	0.925	
b	0.19	0.30	_	
С	0.09	0.20	_	
D	2.90	3.10	3.025	
е	_	_	0.65	
Е	_	_	6.40	
E1	4.30	4.50	4.425	
L	0.45	0.75	0.60	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20



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